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Should be replaced with:

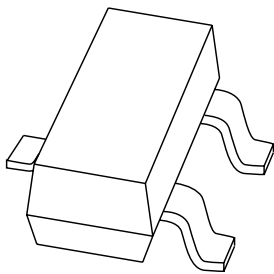
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DATA SHEET



BCW69; BCW70 PNP general purpose transistors

Product data sheet
Supersedes data of 1999 Apr 19

2004 Feb 06

PNP general purpose transistors

BCW69; BCW70

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

PNP transistor in a SOT23 plastic package.
NPN complements: BCW71 and BCW72.

MARKING

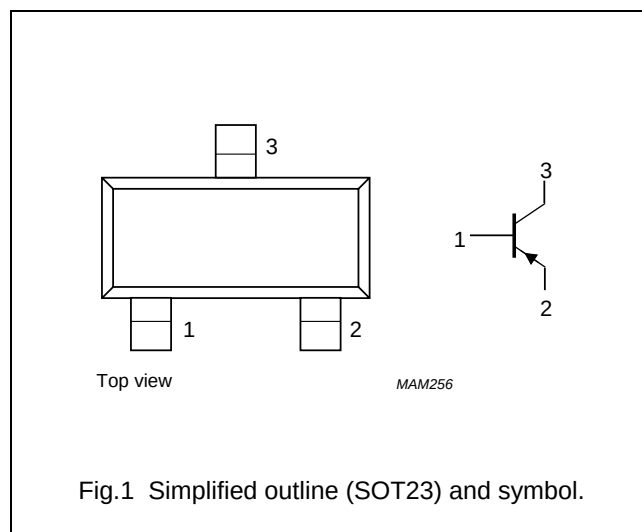
TYPE NUMBER	MARKING CODE ⁽¹⁾
BCW69	H1*
BCW70	H2*

Note

- * = p : Made in Hong Kong.
* = t : Made in Malaysia.
* = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BCW69	–	plastic surface mounted package; 3 leads	SOT23
BCW70			

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–50	V
V_{CEO}	collector-emitter voltage	open base; $I_C = -2$ mA	–	–45	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–100	mA
I_{CM}	peak collector current		–	–200	mA
I_{BM}	peak base current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

PNP general purpose transistors

BCW69; BCW70

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -20\text{ V}$	–	–	–100	nA
		$I_E = 0; V_{CB} = -20\text{ V}; T_j = 100\text{ }^{\circ}\text{C}$	–	–	–10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	–	–	–100	nA
h_{FE}	DC current gain	$I_C = -10\text{ }\mu\text{A}; V_{CE} = -5\text{ V}$	–	90	–	
	BCW69			150	–	
	DC current gain	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V}$	120 215	–	260	
	BCW69 BCW70			–	500	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	–	–80	–300	mV
		$I_C = -50\text{ mA}; I_B = -2.5\text{ mA}; \text{note 1}$	–	–150	–	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	–	–720	–	mV
		$I_C = -50\text{ mA}; I_B = -2.5\text{ mA}; \text{note 1}$	–	–810	–	mV
V_{BE}	base-emitter voltage	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V}$	–600	–	–750	mV
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = -10\text{ V};$ $f = 1\text{ MHz}$	–	4.5	–	pF
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V};$ $f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure	$I_C = -200\text{ }\mu\text{A}; V_{CE} = -5\text{ V};$ $R_S = 2\text{ k}\Omega; f = 1\text{ kHz}; B = 200\text{ Hz}$	–	–	10	dB

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.

PNP general purpose transistors

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PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23

0 1 2 mm
scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	A1 max.	bp	c	D	E	e	e1	HE	Lp	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				04-11-04 06-03-16

PNP general purpose transistors

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: <http://www.nxp.com>

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